

# DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N6477 and 2N6478 types are Epitaxial-Base Silicon Power Transistors designed high voltage amplifier applications.

# <u>MAXIMUM RATINGS</u> $(T_C = 25 °C)$

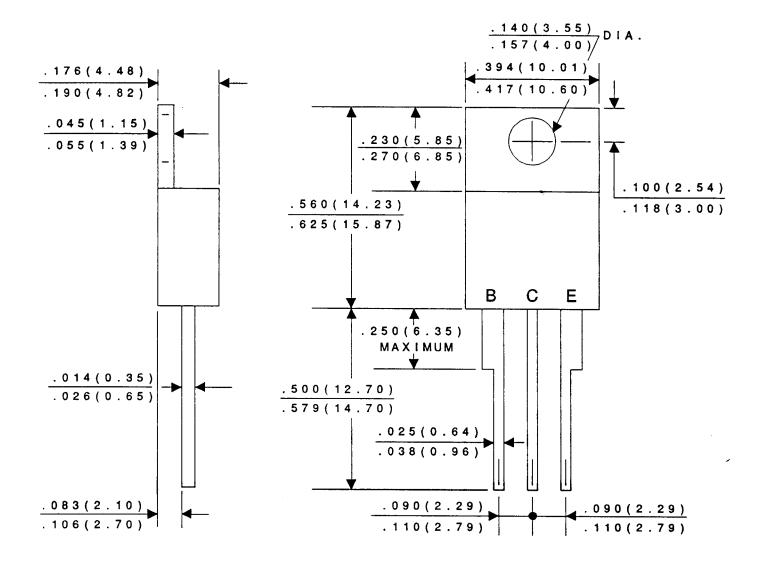
	<u>SYMBOL</u>	<u>2N6477</u>	<u>2N6478</u>	<u>UNITS</u>
Collector-Base Voltage	∨сво	140	160	V
Collector-Emitter Voltage	V <sub>CEV</sub>	140	160	V
Collector-Emitter Voltage	VCEO	130	150	V
Collector-Emitter Voltage	VCER	120	140	V
Emitter-Base Voltage	VEBO	5.0		V
Collector Current	I <sub>C</sub>	2.5		А
Peak Collector Current	<sup>I</sup> CM	4	А	
Base Current	IB	1	А	
Power Dissipation	PD	50		W
Operating and Storage				
Junction Temperature	T <sub>J</sub> ,T <sub>stg</sub>	-65 to +150		°C
Thermal Resistance	Θις	2	.5	٥C/W

# <u>ELECTRICAL CHARACTERISTICS</u> ( $T_C = 25^{\circ}C$ unless otherwise noted)

	<b>-</b>	<u>2N6477</u>		<u>2N6</u>	<u>2N6478</u>	
<u>SYMBOL</u>	TEST CONDITIONS	<u>MIN</u>	<u>MAX</u>	MIN	<u>MAX</u>	<u>UNITS</u>
<sup>I</sup> CEV	V <sub>CE</sub> = 130V, V <sub>BE(off)</sub> = 1.5V		2.0			mA
<b>I</b> CEV	$V_{CE} = 150V, V_{BE(off)} = 1.5V$				2.0	mA
ICEV	V <sub>CE</sub> = 120V, V <sub>BE(off)</sub> = 1.5V, T <sub>C</sub> = 150°C		10			mA
ICEV	V <sub>CE</sub> = 140V, V <sub>BE(off)</sub> = 1.5V, T <sub>C</sub> = 150°C				10	mA
ICEO	V <sub>CE</sub> = 80V		2.0			mA
ICE0	V <sub>CE</sub> = 100V				2.0	mA
I <sub>EBO</sub>	V <sub>BE</sub> = 5.0V		2.0		2.0	mA
BVCEV	I <sub>C</sub> = 100mA, V <sub>BE</sub> = 1.5V	140		160		V
BVCER	I <sub>C</sub> = 100mA, R <sub>BE</sub> = 100Ω	130		150		V
BVCEO	I <sub>C</sub> = 100mA	120		140		V
VCE(SAT)	I <sub>C</sub> = 1.0A, I <sub>B</sub> = 100mA		1.0		1.0	V
V <sub>CE</sub> (SAT)	I <sub>C</sub> = 2.5A, I <sub>B</sub> = 500mA		2.0		2.0	v
VBE(ON)	$V_{CE} = 4.0V, I_{C} = 1.0A$		1.8		1.8	V
V <sub>BE</sub> (ON)	$V_{CE} = 4.0V, I_{C} = 2.5A$		3.0		3.0	V
hFE	$V_{CE} = 4.0V, I_{C} = 1.0A$	25	150	25	150	
hFE	$V_{CE} = 4.0V, I_{C} = 2.5A$	5.0		5.0		
h <sub>fe</sub> l	$V_{CE} = 4.0V, I_{C} = 500 \text{mA}, f = 40 \text{kHz}$	5.0		5.0		
fT	$V_{CE} = 4.0V, I_{C} = 500 \text{mA}$	200	annennen et gryffiger en offisjeffict - S	200	• • •	kHz
h <sub>fe</sub>	$V_{CE} = 4.0V, I_{C} = 100 \text{mA}, f = 1.0 \text{kHz}$	25		25		

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# JEDEC TO-220 CASE - MECHANICAL OUTLINE



All Dimensions in Inches (mm).



# OUTSTANDING SUPPORT AND SUPERIOR SERVICES

#### PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options

### DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free guick ship samples (2<sup>nd</sup> day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- · Environmental regulation compliance
- Customer specific screening
- · Up-screening capabilities

· Custom product packing

Custom bar coding for shipments

- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- · Application and design sample kits
- · Custom product and package development

## REQUESTING PRODUCT PLATING

- If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when 1. ordering (example: 2N2222A TIN/LEAD).
- 2. If requesting Lead (Pb) Free plated devices, add the suffix " PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

## CONTACT US

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